

24V 5A Peak Source and Sink Dual-Channel Driver

1. Features

- Industry standard SOIC-8 pinout
- Two independent gate drive channels
- 5A source and sink peak drive current
- Wide VDD range up to 24V
- Separated enable inputs
- Two channels in parallel for high current driving
- VDD UVLO protection
- TTL and CMOS compatible inputs
- Low propagation delays
- 1ns typical delay matching between two channels
- Outputs held low when floating inputs
- Operating temperature range -40°C to 125°C

2. Applications

- AC/DC and DC/DC converters
- Server and Telecom rectifiers
- EV/HEV inverters and DC/DC converters
- PV boosters and inverters
- UPS
- Motor Control
- Emerging Wide Band-Gap Power Devices

3. Description

The SL27524A is a 5A dual-channel, high-speed, low-side gate driver, capable of effectively and safely driving MOSFETs and IGBTs. Low propagation delay and mismatch and compact SOIC-8 package enables MOSFETs to switch at hundreds of kHz. It is very suitable for server and telecom power supply's synchronous rectification driving, where synchronous MOSFET's dead time accuracy directly impacts converter's efficiency. The driver is capable to parallel two channels to increase output driving current. The input thresholds are based on TTL with voltage tolerance from -5V to 20V.

Wide VDD operating range from 4.5V to 20V enables effective driving with MOSFET or GaN power switches. Integrated UVLO protection ensures output held at low under abnormal conditions.

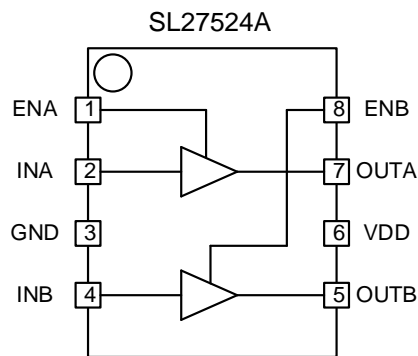
The independent inputs ranges from -5V to 24V ensure robust operation with undershoot or overshoot induced by parasitic inductances. The input thresholds are compatible with TTL input.

Device Information

PART NUMBER	PACKAGE	PACKING
SL27524A	SOIC-8	Tape and Reel

Pin Configuration

Dual Non-Inverting Inputs



4. Pin Configuration and Functions

PIN	NAME	I/O	DESCRIPTION
1	ENA	I	Channel A enable input
2	INA	I	Channel A input
3	GND	G	Driver ground
4	INB	I	Channel B input
5	OUTB	O	Channel B driver output
6	VDD	P	Positive bias supply
7	OUTA	O	Channel A driver output
8	ENB	I	Channel B enable input

Truth Table

VDD is higher than UVLO threshold.

ENx	INx	OUTx
L	X	L
H or floating	L or floating	L
H or floating	H	H

5. Specifications

5.1 Absolute Maximum Ratings

Over free-air temperature range (unless otherwise noted) ⁽¹⁾

		MIN	MAX	UNIT
V _{DD}	Total supply voltage (reference to GND)	-0.3	24	V
OUTA, OUTB	Gate driver output voltage	-0.3	V _{DD} +0.3	V
INA, INB	Signal input voltage	-5	24	V
ENA, ENB	Enable control signal	-5	24	V
T _J	Junction temperature	-40	150	°C
T _{STG}	Storage temperature	-65	150	°C

(1) Operating beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended period may affect device reliability.

5.2 ESD Rating

		Value	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
 (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operation Conditions

		MIN	MAX	UNIT
V _{DD}	Supply voltage	4.5	20	V
V _{INx} , EN _x	Input voltage	0	20	V
T _A	Ambient temperature	-40	125	°C

5.4 Thermal Information

		UNIT
R _{θJA}	Junction-to-Ambient	128 °C/W
R _{θJB}	Junction-to-PCB	68.5 °C/W

5.5 Electrical Specifications

Unless otherwise noted, $V_{DD} = 12\text{ V}$, $T_A = -40^\circ\text{C}$ to 125°C

Currents are positive into and negative out of the specified terminal. Typical condition specifications are at 25°C .

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
BIAS CURRENT						
I _{DDoff}	Startup current	VDD=3V, INA=INB=0V	30			μA
I _{DDq}	Quiescent current	INA=INB=0V	0.6			mA
UVLO						
V _{ON}	Under voltage thresholds	Rising threshold		3.8	4.2	V
V _{OFF}		Falling threshold	3.2	3.5		
INPUT (INA, INB)						
V _{INH}	Input rising threshold			1.96	2.4	V
V _{INL}	Input falling threshold		0.8	1.15		V
V _{INHYS}	Input hysteresis			0.8		V
V _{INNS}	Input negative voltage capability		-5			V
ENABLE INPUT (ENA, ENB)						
V _{ENH}	Enable input rising threshold			1.92	2.2	V
V _{ENL}	Enable input signal threshold		0.8	1.2		V
V _{INHYS}	Enable input hysteresis			0.7		V
OUTPUTS (OUTA, OUTB)						
I _o	Peak source and sink currents	C _{LOAD} =0.22uF, with external current limiting resistors, 1kHz switching frequency	5			A
V _{OH}	Output high voltage	I _{OUTH} = -10mA	V _{DD} -0.007 V _{DD} -0.03			V
V _{OL}	Output low voltage	I _{OUTL} = 10mA	0.005 0.012			V
R _{OH}	Output static pull-up resistance		0.7 3			Ω
R _{OL}	Output pull-down resistance		0.5 1.2			Ω
Timing						
T _{Drr}	Rising delay	C _{LOAD} = 1.8nF	16		30	ns
T _{Dff}	Falling delay		16		30	
T _r	Rise time	C _{LOAD} = 1.8nF	8		12	ns
T _f	Fall time		8		12	
T _{dm}	Delay mismatch	INA=INB, ENA=ENB=VDD	1			ns

6. Typical Characteristics

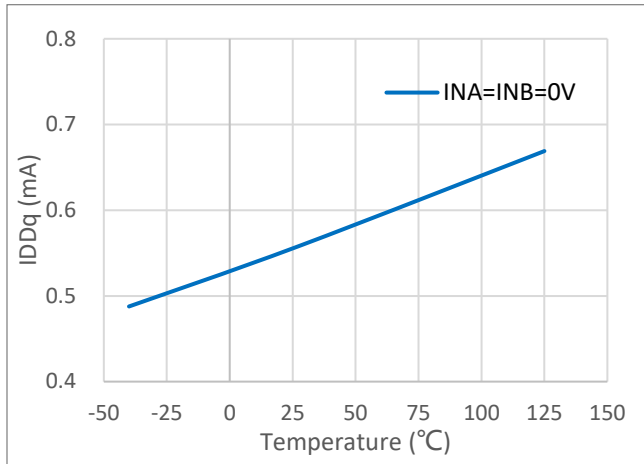


Figure 1. Quiescent Current $IDDq$ vs Temperature

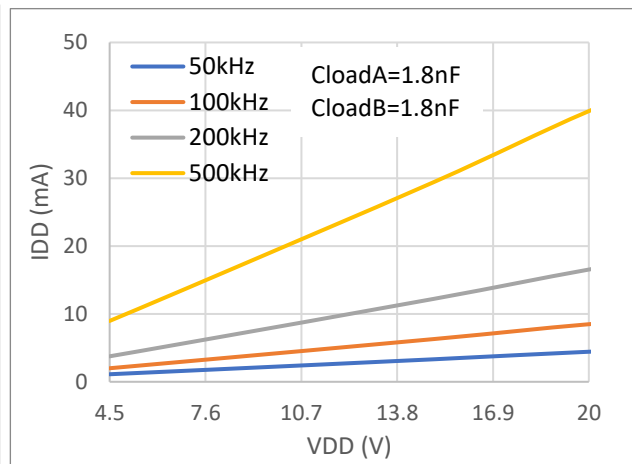


Figure 2. Operating Current IDD vs VDD

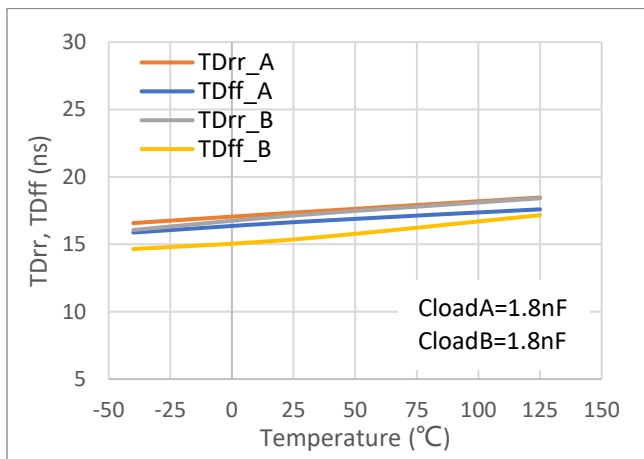


Figure 3. Propagation Delay vs Temperature

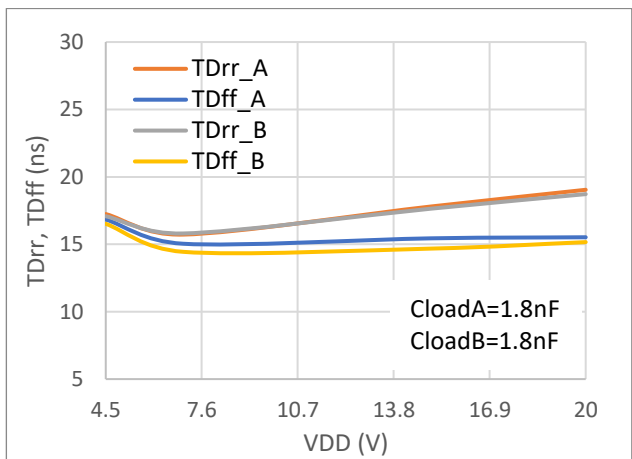


Figure 4. Propagation Delay vs VDD

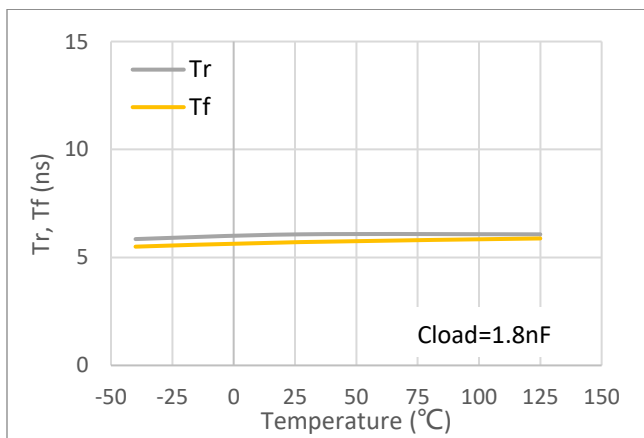


Figure 5. Rise Time and Fall time vs Temperature

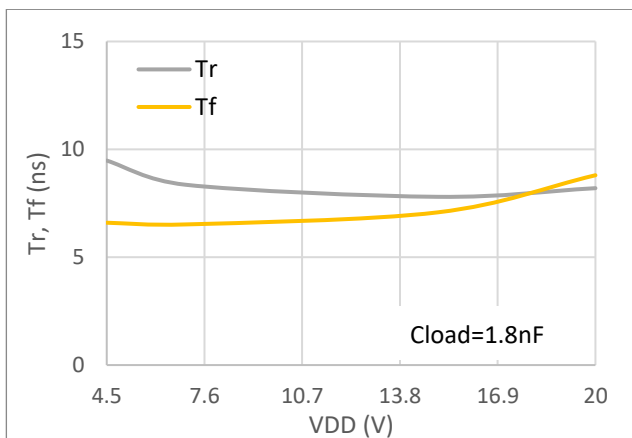
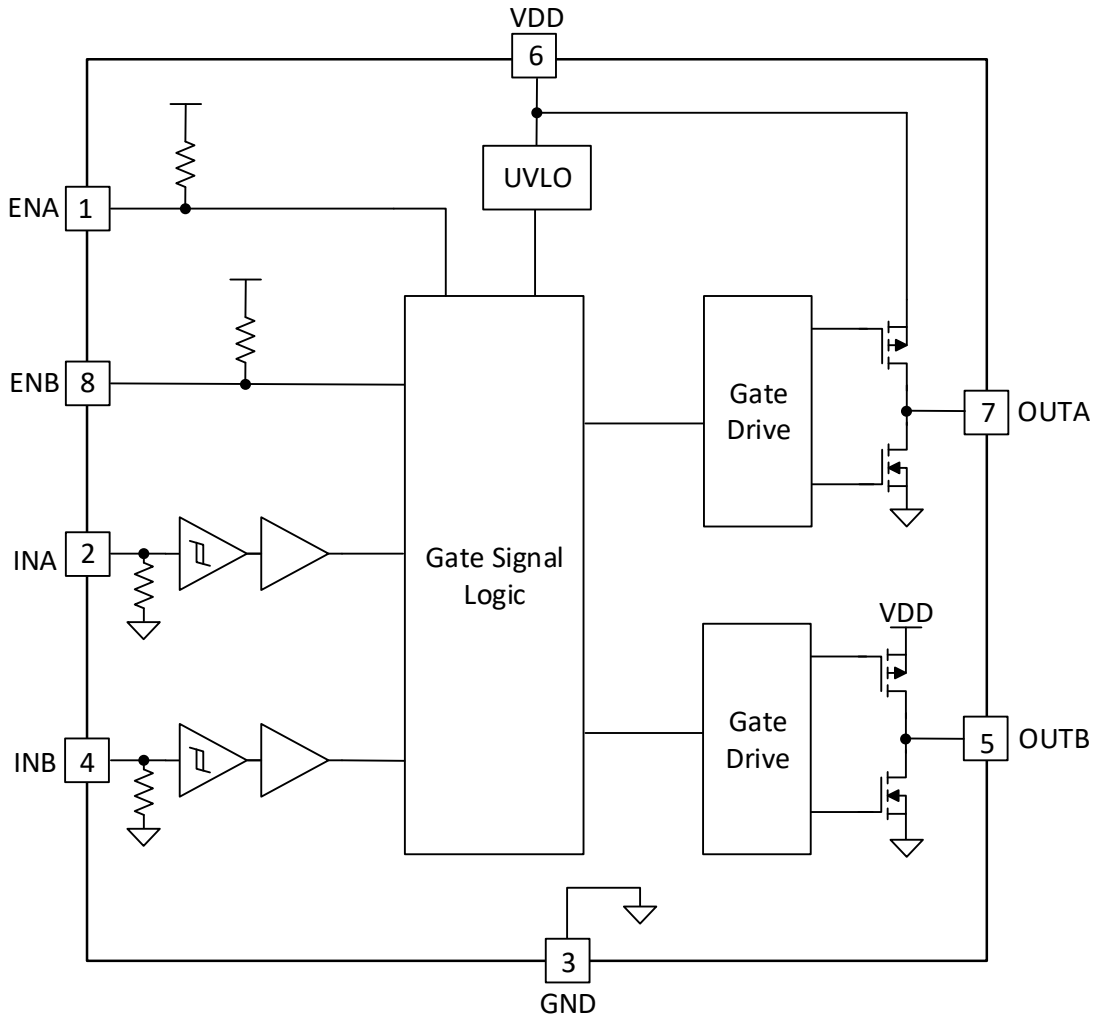


Figure 6. Rise Time and Fall time vs VDD

7. Detail Descriptions

SL27524A driver provides dual-channel high-speed low-side gate drive. It features tight mismatching outputs when two channels are paralleled to drive large or paralleled power switches.

Function Block Diagram



7.1 Input Signals INA and INB

INA and INB are non-inverting logic gate driver inputs. The pins have a weak pulldown. When left floating, outputs are pulled to GND. The input is a TTL and CMOS logic level with maximum 24V input tolerance.

7.2 Enable Signals ENA and ENB

ENA and ENB are enable control signals. When ENx is driven low the OUTx is pulled to GND. When ENx is driven high the OUTx follows INx. The enable pins have a weak pullup. When left floating, outputs follow inputs. The enable signal is a TTL and CMOS logic level with maximum 24V input tolerance.

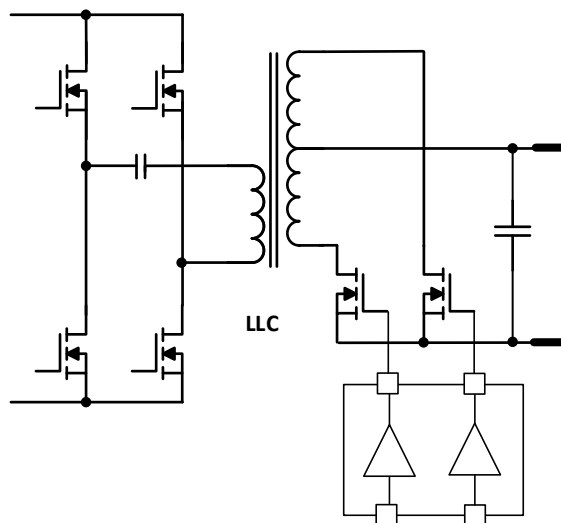
7.3 OUTA and OUTB

OUTA and OUTB are totem-pole outputs, which consist of a P-channel MOSFET for pullup and an N-channel MOSFET for pulldown. Each output stage in SL27524A can supply 5A peak source and 5A peak sink current pulses. The output voltage swings between VDD and GND providing rail-to-rail operation. The presence of the MOSFET body diodes also offer voltage clamping paths to limit overshoot and undershoot. That means that in many cases, external Schottky diode clamps may not be necessary.

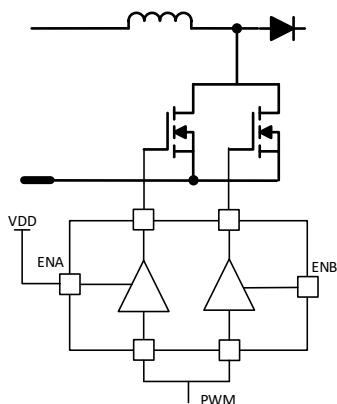
7.4 VDD and Under Voltage Protection

SL27524A maximum voltage rating is 24V. It is suitable for Si MOSFET, IGBT and SiC MOSFET gate drive. The driver has internal under voltage lockout (UVLO) protection feature. When VDD level is below UVLO threshold, this circuit holds the output LOW, regardless of the status of the inputs.

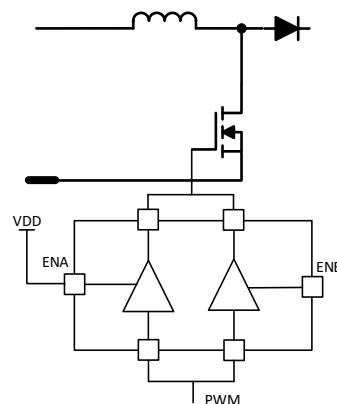
8. Application Implementation



Two channels driven separately

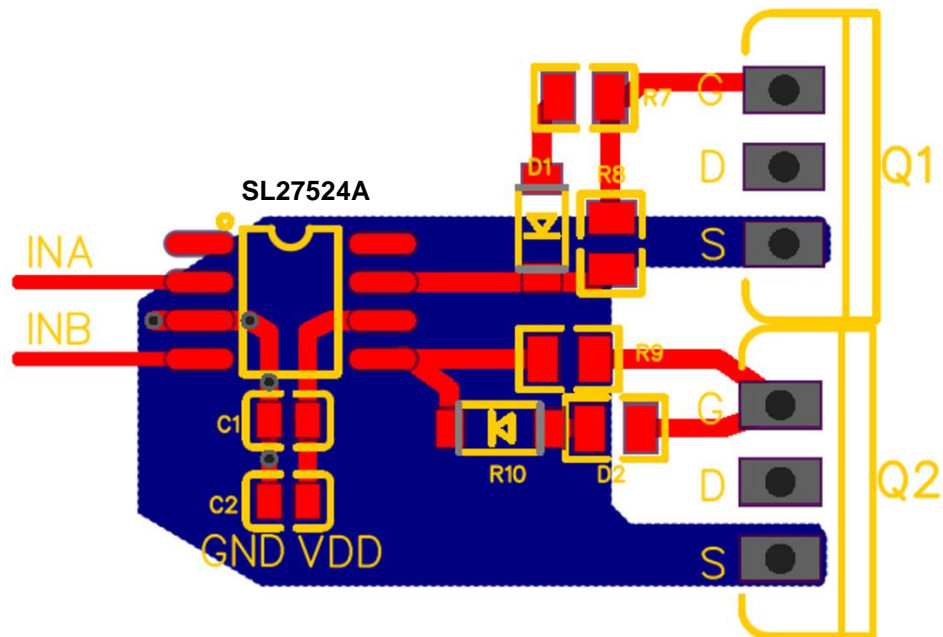


Two paralleled switches driven by two outputs with minimized mismatch



A large switch driven by two paralleled outputs with minimized mismatch

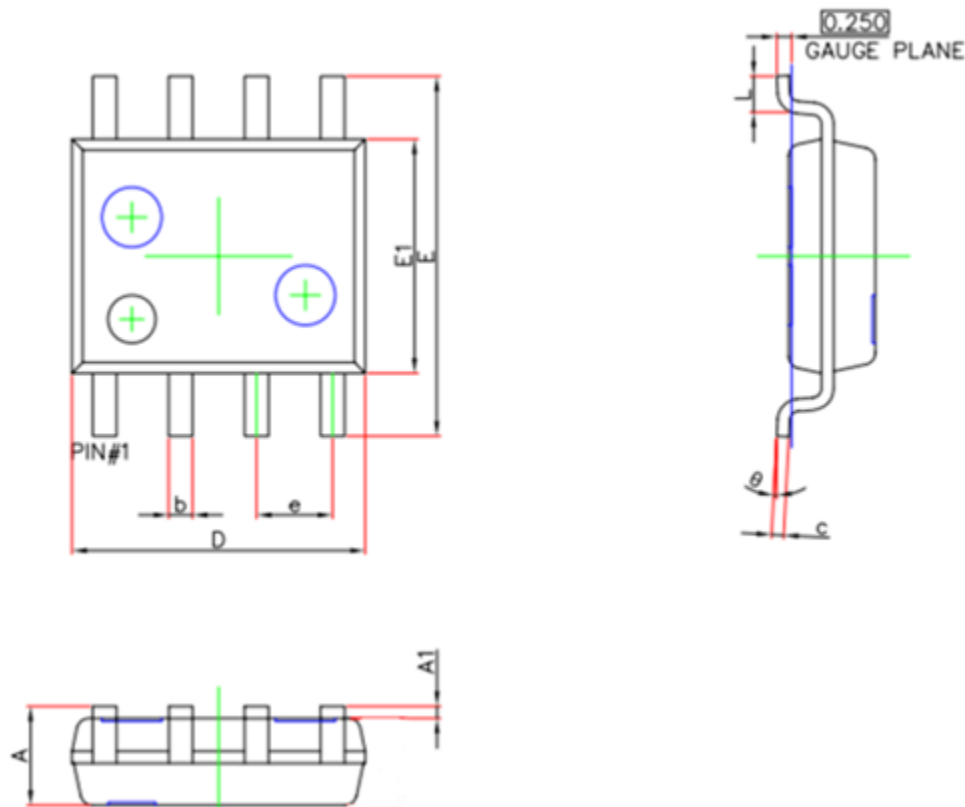
9. Layout



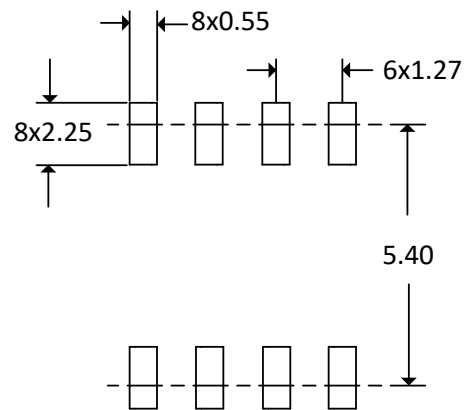
Layout Example for SL27524A

10. Package Information

SOIC-8 Package Dimensions



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.110	0.250	0.004	0.010
b	0.310	0.510	0.012	0.020
c	0.130	0.250	0.005	0.010
D	4.810	5.000	0.189	0.197
E	5.800	6.190	0.228	0.244
E1	3.810	3.980	0.150	0.157
e	1.270		0.050	
L	0.410	1.270	0.016	0.050
θ	0.000	8.000	0.000	0.315



SOIC-8 Recommended Soldering Dimensions